FUJITSU GENERAL ELECTRONICS LIMITED FGI-61020E065D1

IGBT MODULE 650V/20A IPM

■ Features

- · DC input, 3-phase AC output IGBT IPM
- Built -in various protection functions (Over current protection, Over heating protection, Under voltage protection)
- Short -circuit warranty type IGBT (5µs/125°C)
- · Reliability improvement by epoxy resin encapsulation



Dimensions

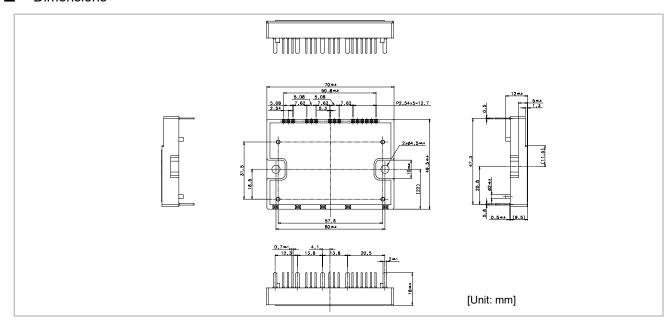


Fig.1. Dimensions

Pin Functions

Pin No.	Name	Function	Pin No.	Name	Function
1	GND U	Ground terminal (U)	9	Vcc W	Power supply (W)
2	Vin U	Driver input (U)	10	GND	Ground terminal (Under arm)
3	Vcc U	Power supply (U)	11	Vcc	Power supply for Under arm
4	GND V	Ground terminal (V)	12	Vin X	Driver input (X)
5	Vin V	Driver input (V)	13	Vin Y	Driver input (Y)
6	Vcc V	Power supply (V)	14	Vin Z	Driver input (Z)
7	GND W	Ground terminal (W)	15	ALM	Alarm output
8	Vin W	Driver input (W)			

■ Block Diagram

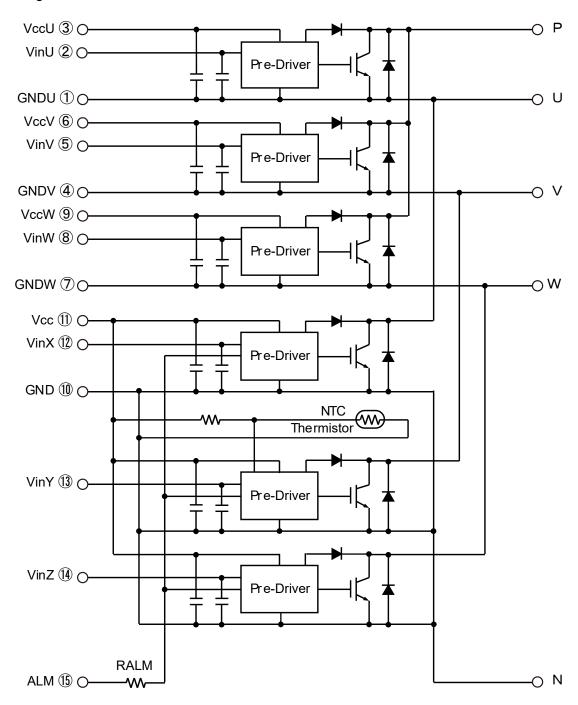


Fig.2. Block Diagram

■ Absolute Maximum Ratings (Tc=25°C, Vcc=15V unless otherwise specified)

Items		Symbol	Min.	Max.	Units
Collector-Emitter Voltage (*1)			0	650	V
Short Circuit Voltage			200	400	V
	DC	Ic	-	20	Α
Collector Current	1ms	Icp	-	40	Α
	Duty=100%(*2)	-lc	-	20	Α
Collector Power Dissipation	1 device (*3)	Pc	-	88	W
Supply Voltage of Pre-Driver (*4)			-0.3	20	V
Input Signal Voltage (*5)		Vin	-0.3	Vcc+0.5	V
Alarm Signal Voltage (*6)		Valm	-0.3	Vcc	V
Alarm Signal Current (*7)		IALM	ı	20	mA
Junction Temperature		Tj	ı	150	Ŝ
Operating Case Temperature		Topr	-20	110	°C
Storage Temperature		Tstg	-40	125	Ŝ
Solder Temperature (*8)		Tsol	-	260	°C
Isolating Voltage (*9)		Viso	-	AC2500	Vrms
Screw Torque	Mounting (M4)	-	-	1.7	Ν·m

Note*1: Vces shall be applied to the input voltage between terminal P-(U,V,W) and (U,V, W)-N.

Note*4: Vcc shall be applied to the input voltage between terminal No.3 and 1, 6 and 4, 9 and 7, 11 and 10.

Note*5: Vin shall be applied to the input voltage between terminal No.2 and 1, 5 and 4, 8 and 7, 12 - 14 and 10.

Note*6: Valm shall be applied to the voltage between terminal No.15 and 10.

Note*9: Terminal to base, 50/60Hz sine wave 1min. All terminals should be connected together during the test.

■ Electrical Characteristics (Tj=25°C Vcc=15V unless otherwise specified)

Items	Symbol	Conditions		Min.	Тур.	Max.	Units
Collector Current at off signal		Vce=650V		-	-	1.0	mA
Collector-Emitter saturation		Ic=20A	Terminal	-	-	2.25	V
Collector-Emitter Saturation	V _{CE(sat)}	IC-ZUA	Chip	-	1.65	•	V
Forward voltage of FWD	VF	I==20A	Terminal	-	-	2.05	V
Forward voltage of FWD			Chip	-	1.45	1	V
	ton	VDC=300V, Tj=125°C, Ic=20A		1.1	-	-	μs
Switching time	toff	VDC=300V, 1j=123 (5, IC-20A	-	-	2.1	μs
	trr	V _{DC} =300V, I _F =20A		-	-	0.4	μs
Supply current of P-slde pre-drlver (per one unit)	Iccp	Switching Frequency=0-15kHz		-	-	13	mA
Supply current of N-side pre-driver	Iccn	Tc=-20~110°C		-	-	38	mA
Input signal threshold voltage	V _{inth(on)}	Vin-GND	ON	1.2	1.5	1.6	V
Input signal tilleshold voltage	V _{inth(off)}	VIII-GIND	OFF	1.5	1.65	1.9	V
Over Current Protection Level	loc	T _j =125°C		30	-	•	Α
Over Current Protection Delay time	t _{dOC}	T _j =125°C		-	1.5	ı	μs
Short Circuit Protection Delay time	tsc	T _j =125°C		-	4	5	μs
Over Heating Protection Temperature Level	Тон	Module center		140	-	ı	°C
Over Heating Protection Hysteresis	Тн			-	20	-	°C
Under Voltage Protection Level	Vuv			11.0	-	12.5	V
Under Voltage Protection Hysteresis	Vн			0.2	0.5	-	V
	t _{ALM(OC)}	ALM-GND		1.0	1.3	(1.6)	ms
Alarm Signal Hold Time	t _{ALM(UV)}	Tc=-20~110°C	Vcc≧10V	2.5	2.9	(3.2)	ms
	t _{ALM(Toh)}	1020~110 C		5.0	5.6	(6.2)	ms
Resistance for current limit	RALM			1170	1300	1430	Ω

Figures in () are reference values.

Note*2: Duty=125°C/Rth(j-c)D /(If×Vf Max.)×100

Note*3: Pc=125°C/Rth(j-c)Q

Note*7: IALM shall be applied to the input current to terminal No.15.

Note*8: Immersion time 10 ± 1sec.1time.

■ Thermal Characteristics (Tc= 25°C)

Items			Symbol	Min.	Тур.	Max.	Units
lumation to Coop Thormal Decisions (*)	Invertor	IGBT	R _{th(j-c)Q}	-	-	1.41	°C/W
Junction to Case Thermal Resislance (*)		FWD	R _{th(j-c)D}	-	-	1.63	°C/W
Case to Fin Thermal Resistance with Compound			R _{th(c-f)}	-	0.17	-	°C/W

Note *: For 1 device, the measurement point of the case is just under the chip.

■ Recommended Operating Conditions

Items	Symbol	Min.	Тур.	Max.	Units
DC Bus Voltage	V _{DC}	1	•	400	V
Power Supply Voltage of Pre-Driver	Vcc	13.5	15.0	16.5	V
Switching frequency of IPM	fsw	-	-	20	kHz
Arm shoot through blocking time for IPM's Input signal	t _{dead}	1.0	-	-	μs
Screw Torque (M4)	-	1.3	-	1.7	N·m

■ Weight

Items	Symbol	Min.	Тур.	Max.	Units
Weight	Wt	-	80	-	q

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- (4) Please pay special attention to the operational power source voltage range, category temperature/humidity range when using this product. If used exceeding the guaranteed values, we are not liable for any defect or breakdown that has happened after the use. Even if used within the guaranteed values, be sure to have redundancy design with which equipment using our product is not contrary to various laws due to operation of our product.